

AMENDMENTS TO THE SPECIFICATION

Please replace Paragraph [0001], which starts with “This application is a division...”,
5 with the following amended text:

This application is a division of application Serial No. 10/249,864 filed on May
13, 2003, now U.S. Pat. No. 6,737,700.

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Please replace Paragraph [0006], which starts with “Fig.1 is a sectional schematic
diagram illustrating...”, with the following amended paragraph:

15 Fig.1 is a sectional schematic diagram illustrating a prior art non-volatile memory
cell structure1. As shown in Fig.1, prior art non-volatile memory cell structure1
includes a substrate 10, a tunneling oxide layer 11 formed on the substrate 10, a
floating gate 12 formed on the tunneling oxide layer 11, a dielectric layer 13, and a
control gate 14. A drain region 15 and a source region 16 are provided in the substrate
20 10.